



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

IZUMI, Katsutoshi, et al.

Group Art Unit: **2823**

Serial No.: **10/708,593**

Examiner: **Michelle ESTRADA**

Filed: **March 12, 2004**

P.T.O. Confirmation No.: **2592**

For: **METHOD FOR MANUFACTURING BURIED INSULATING LAYER
TYPE SINGLE CRYSTAL SILICON CARBIDE SUBSTRATE (AS AMENDED)**

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: February 7, 2005

Sir:

This is a Preliminary Amendment for the above-captioned patent application. Please amend the above-captioned patent application as follows:

Amendments to the Title of the Invention begin on page 2 of this paper.

Remarks/Arguments begin on page 3 of this paper.

AMENDMENTS TO THE TITLE:

Amend the title to read as follows:

METHOD FOR MANUFACTURING BURIED INSULATING LAYER TYPE
SINGLE CRYSTAL SILICON CARBIDE SUBSTRATE ~~AND~~
~~MANUFACTURING DEVICE FOR THE SAME~~